

WORCESTER POLYTECHNIC INSTITUTE MECHANICAL ENGINEERING DEPARTMENT

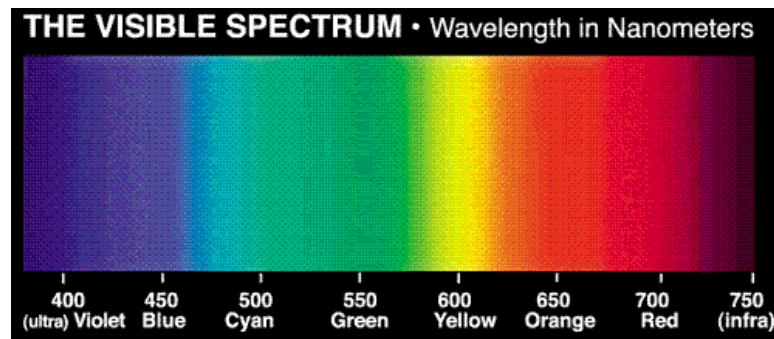
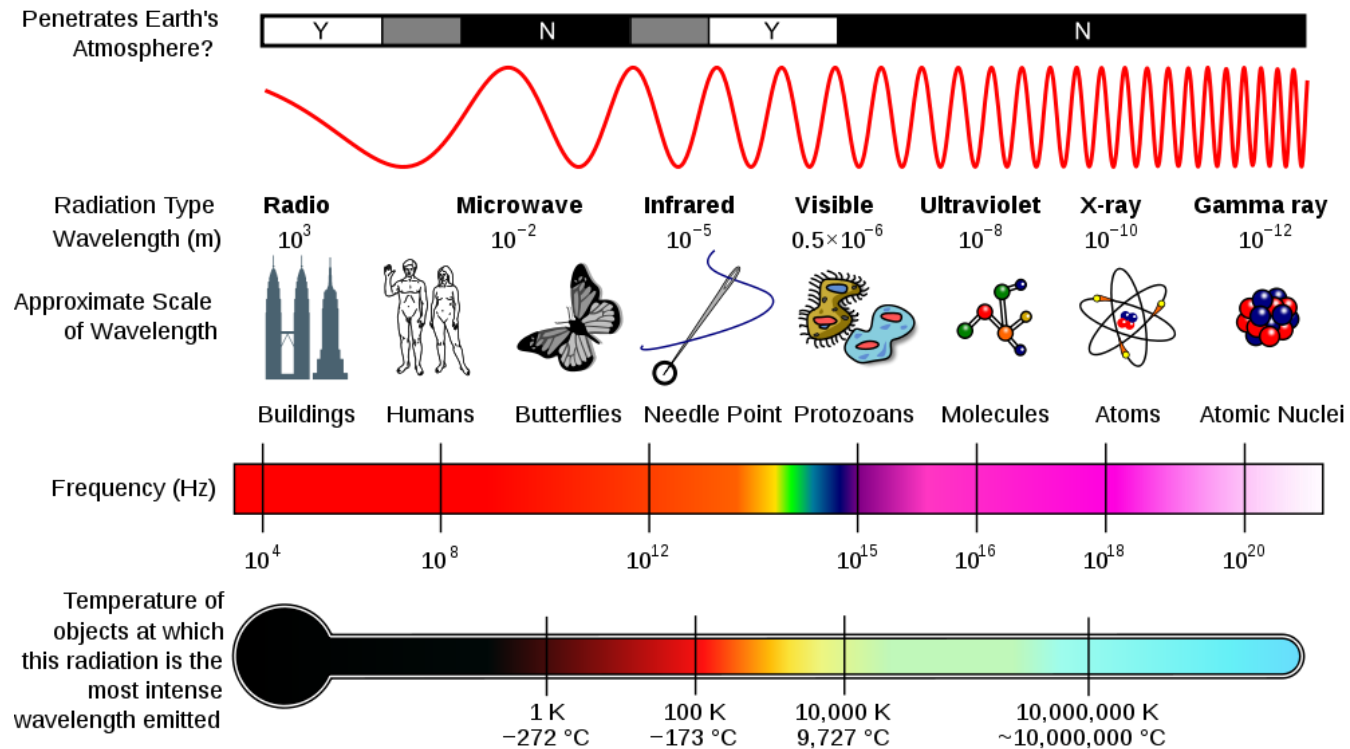
Optical Metrology and NDT
ME-593 / ME-5304, C'2025

Lecture 02
January 2025



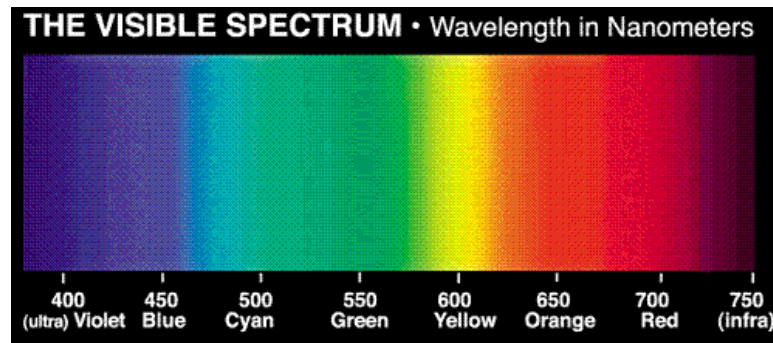
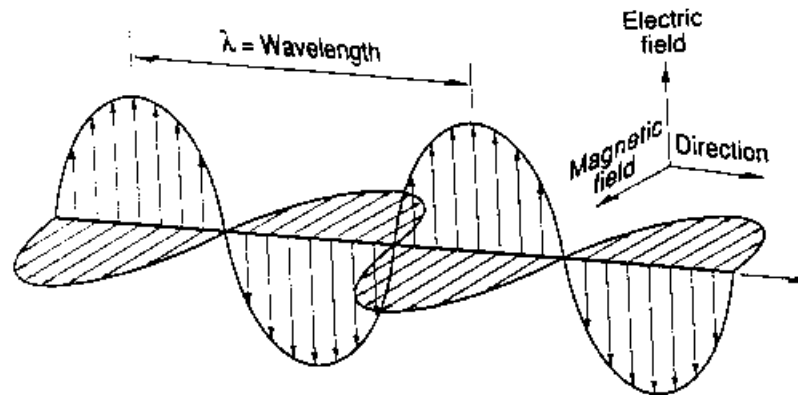
Light Sources

Electromagnetic spectrum



Light Sources

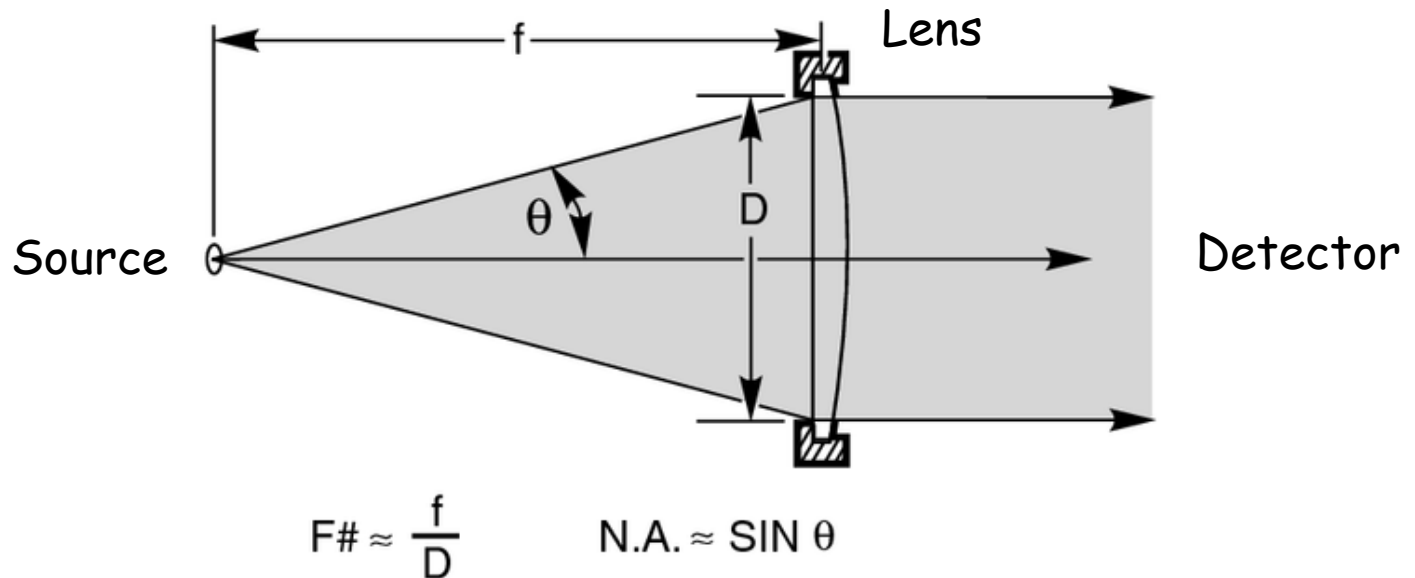
Electromagnetic spectrum



Light Sources

Collection and collimation

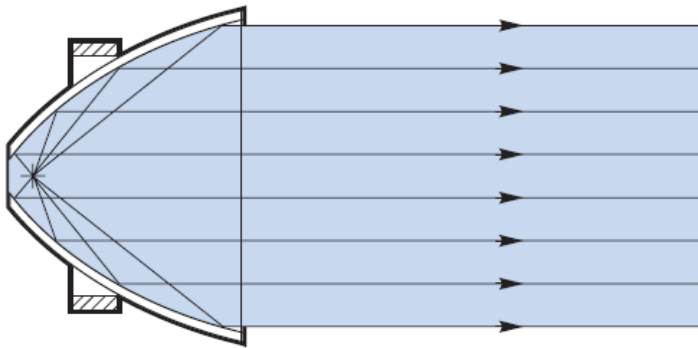
Lens: collecting and collimating light from a source



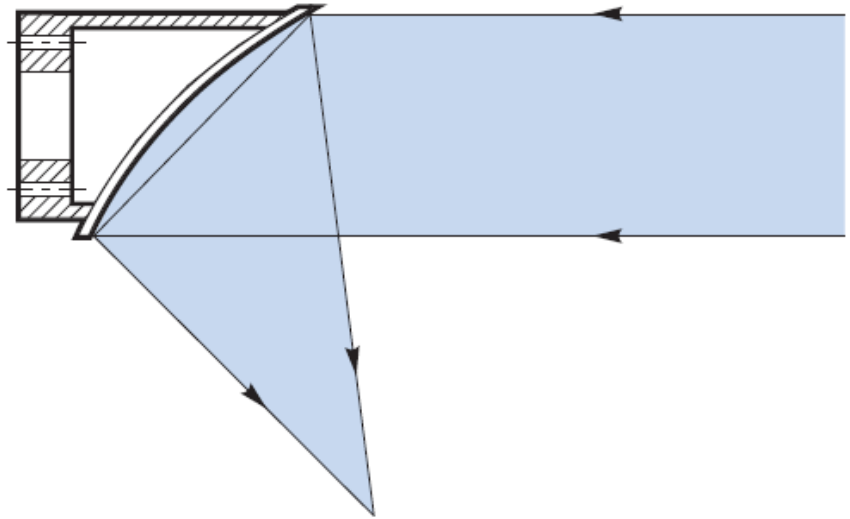
Light Sources

Reflectors

Parabolic reflectors



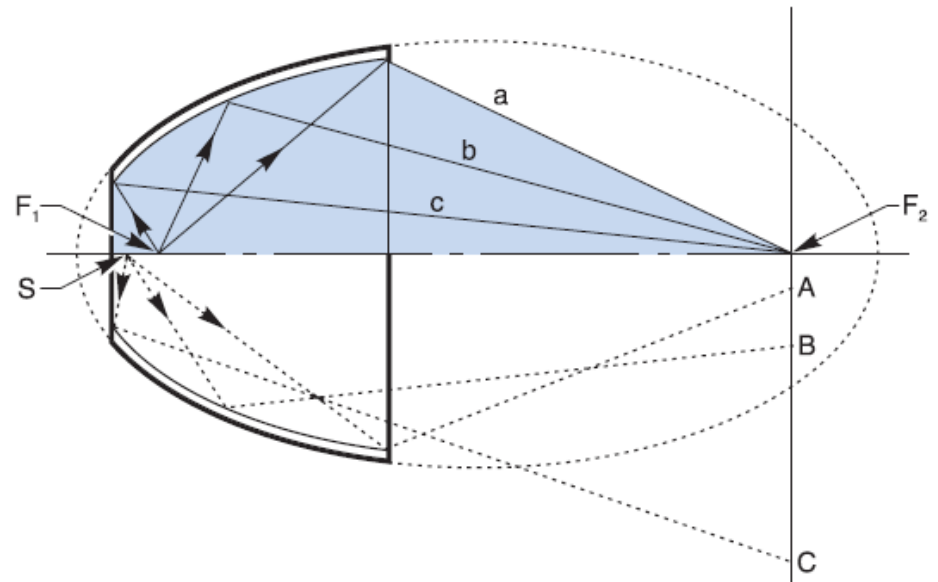
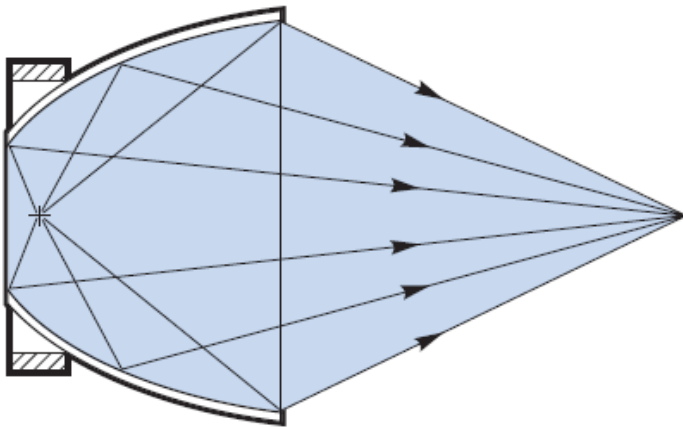
SOURCE AT FOCUS



Light Sources

Reflectors

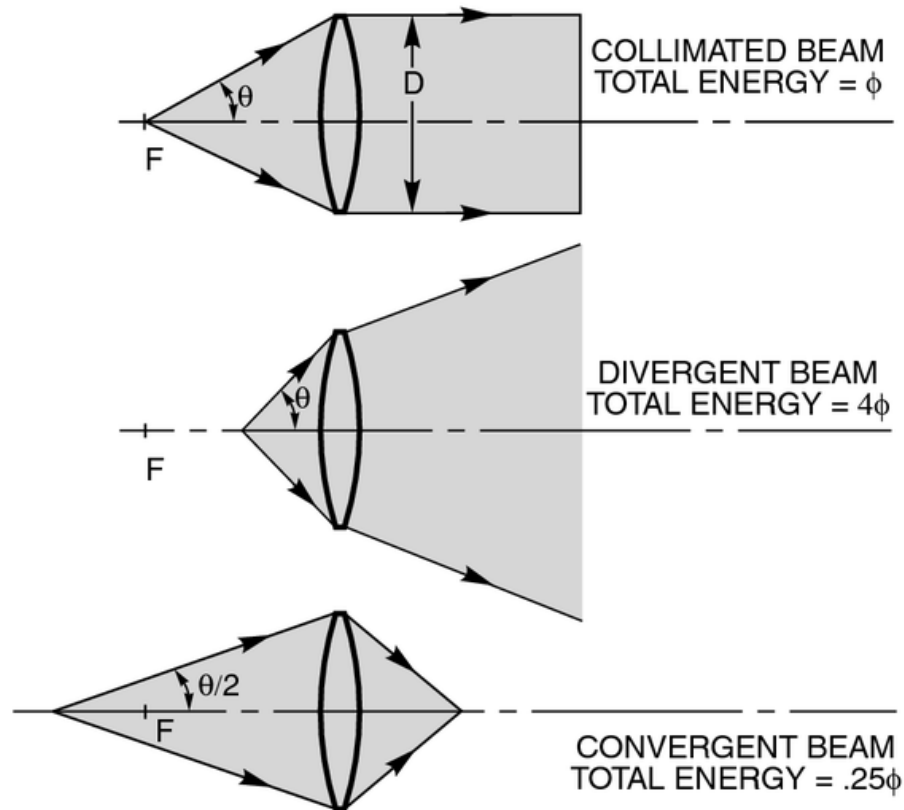
Ellipsoidal reflectors



Light Sources

Irradiance

Light collection by a lens at three different distances from a source

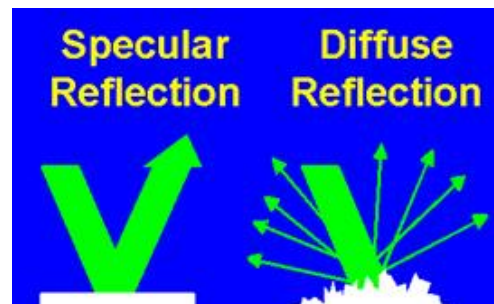
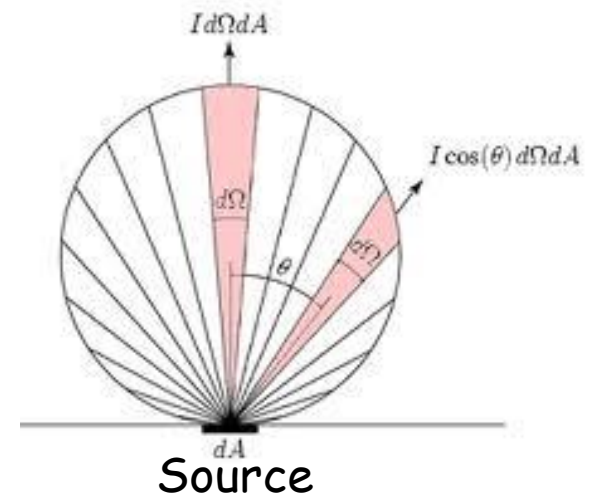
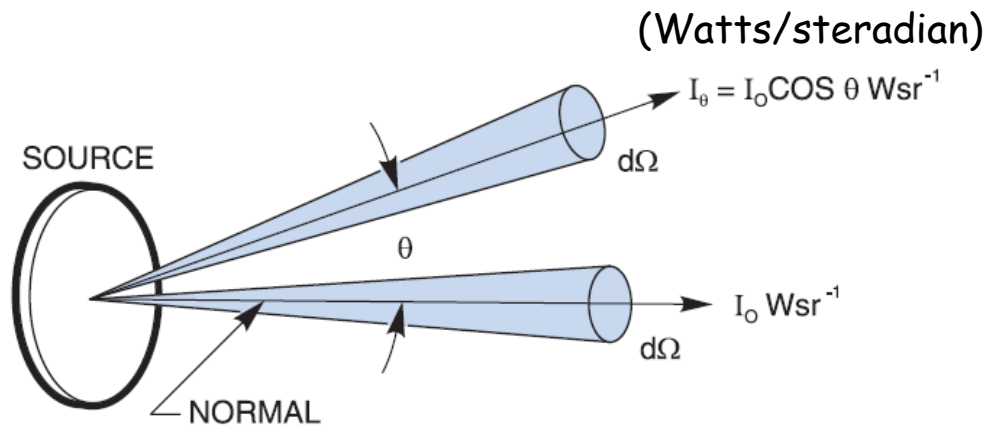


Light Sources

Irradiance

Lambert's Law

Lambert's Cosine Law holds that the radiation per unit solid angle (the radiant intensity) from a flat surface varies with the cosine of the angle to the surface normal



Light Sources

Irradiance

Commonly used Radiometric, Photometric, and Photon quantities

Radiometric			Photometric			Photon		
Quantity	Usual Symbol	Units	Quantity	Usual Symbol	Units	Quantity	Usual Symbol	Units
Radiant Energy	Q_e	J	Luminous Energy	Q_v	lm s	Photon Energy	N_p	*
Radiant Power or Flux	ϕ_e	W	Luminous Flux	ϕ_v	lm	Photon Flux	$\Phi_p = \frac{dN_p}{dt}$	s^{-1}
Radiant Exitance or Emittance	M_e	$W\ m^{-2}$	Luminous Exitance or Emittance	M_v	$lm\ m^{-2}$	Photon Exitance	M_p	$s^{-1}\ m^{-2}$
Irradiance	E_e	$W\ m^{-2}$	Illuminance	E_v	lx	Photon Irradiance	E_p	$s^{-1}\ m^{-2}$
Radiant Intensity	I_e	$W\ sr^{-1}$	Luminous Intensity	I_v	cd	Photon Intensity	I_p	$s^{-1}\ sr^{-1}$
Radiance	L_e	$W\ sr^{-1}\ m^{-2}$	Luminance	L_v	$cd\ m^{-2}$	Photon Radiance	L_p	$s^{-1}\ sr^{-1}\ m^{-2}$

* Photon quantities are expressed in number of photons followed by the units, eg. photon flux (number of photons) s^{-1} . The unit for photon energy is number of photons.

The subscripts e,v, and p designate radiometric, photometric, and photon quantities respectively. They are usually omitted when working with only one type of quantity.

Symbols Key:

J: joule

W: watts

m: meter

sr: steradian

lm: lumen

s: second

cd: candela

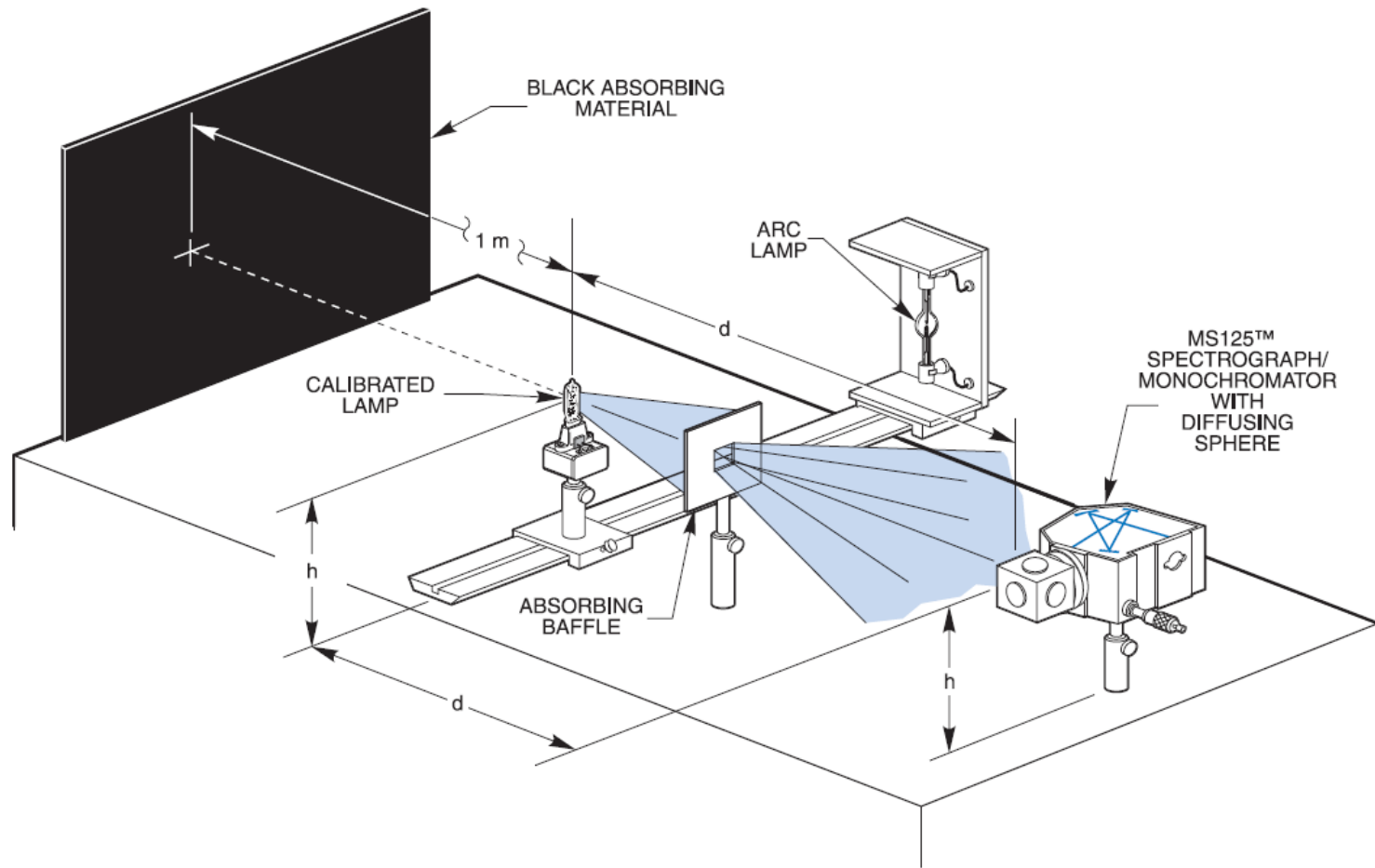
lx: lux, lumen m^{-2}



Light Sources

Irradiance

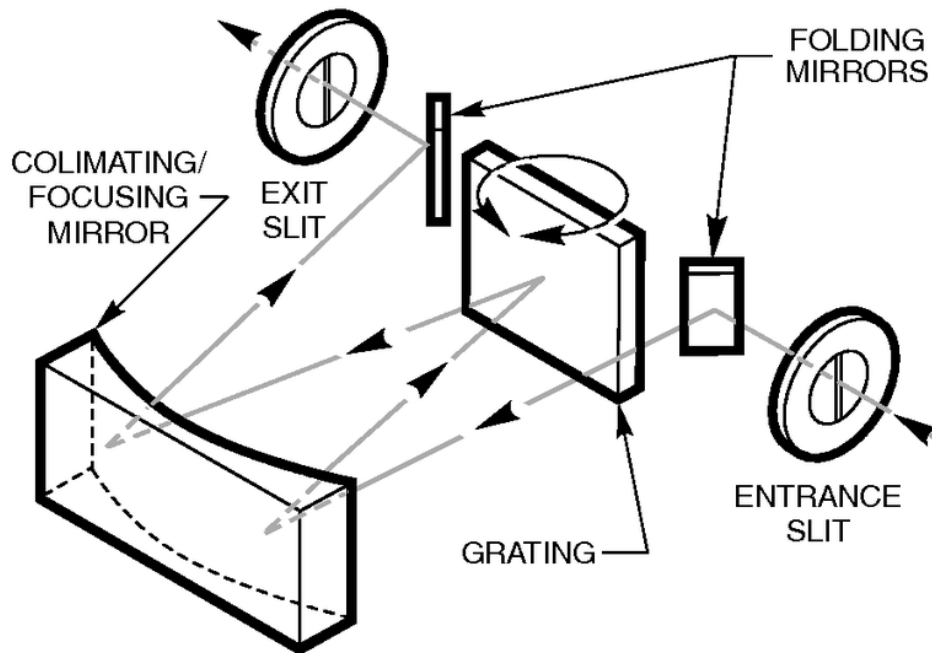
Setup for radiometric measurements



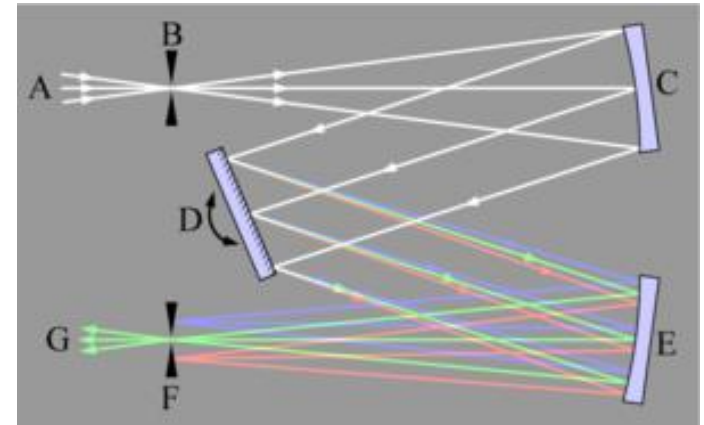
Light Sources

Irradiance

Typical monochromators



Entrance slit



Exit slit

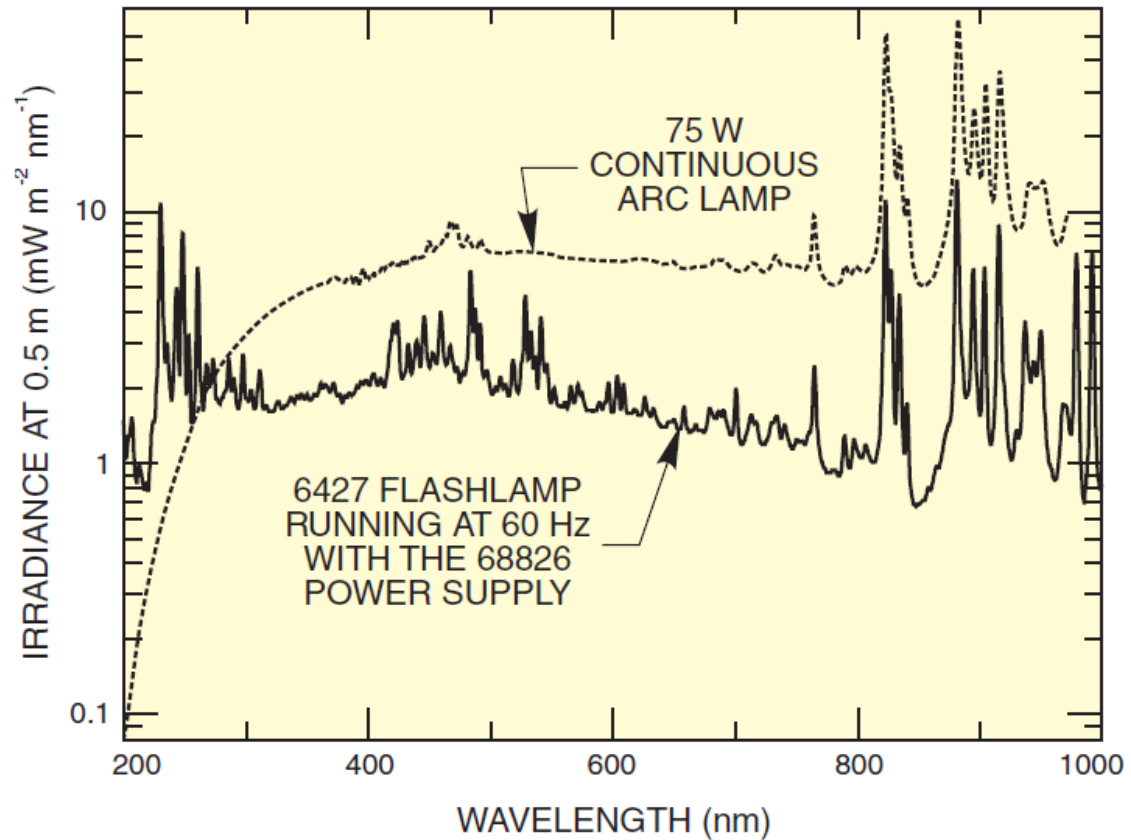


Light Sources

Irradiance

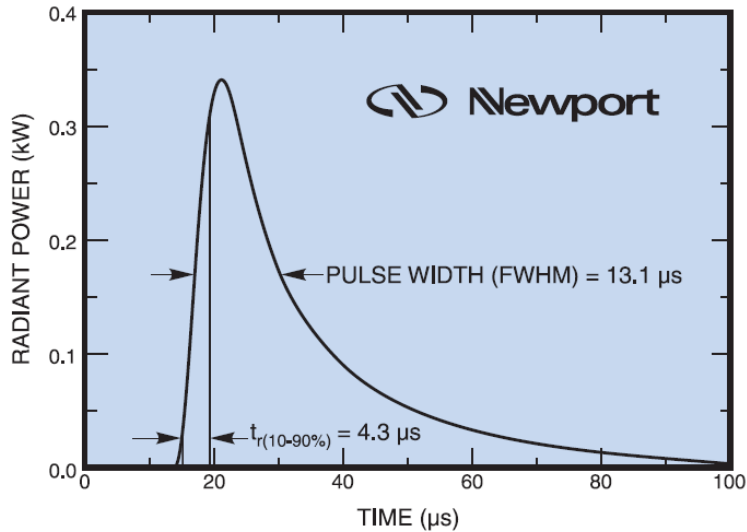


6426 and 6427 Xenon Flashlamps, with 68826 Power Supply.



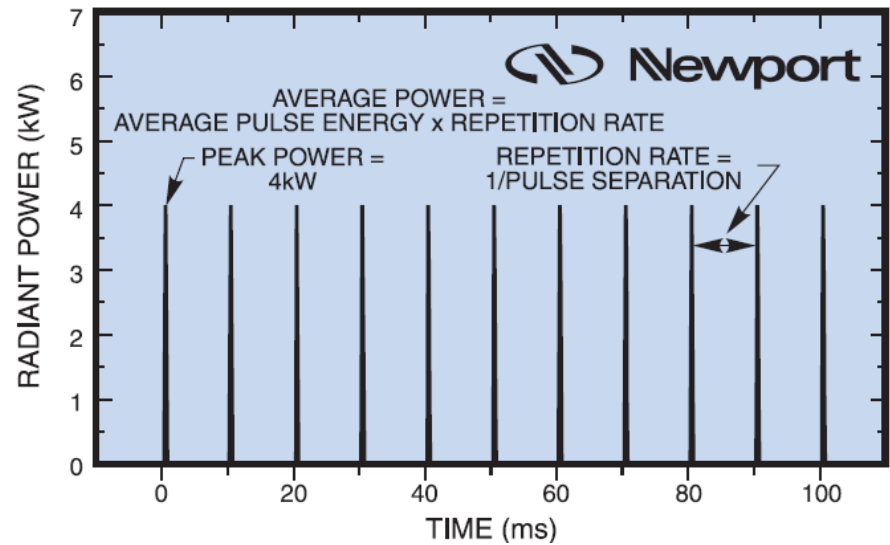
Light Sources

Pulsed source



Typical single pulse

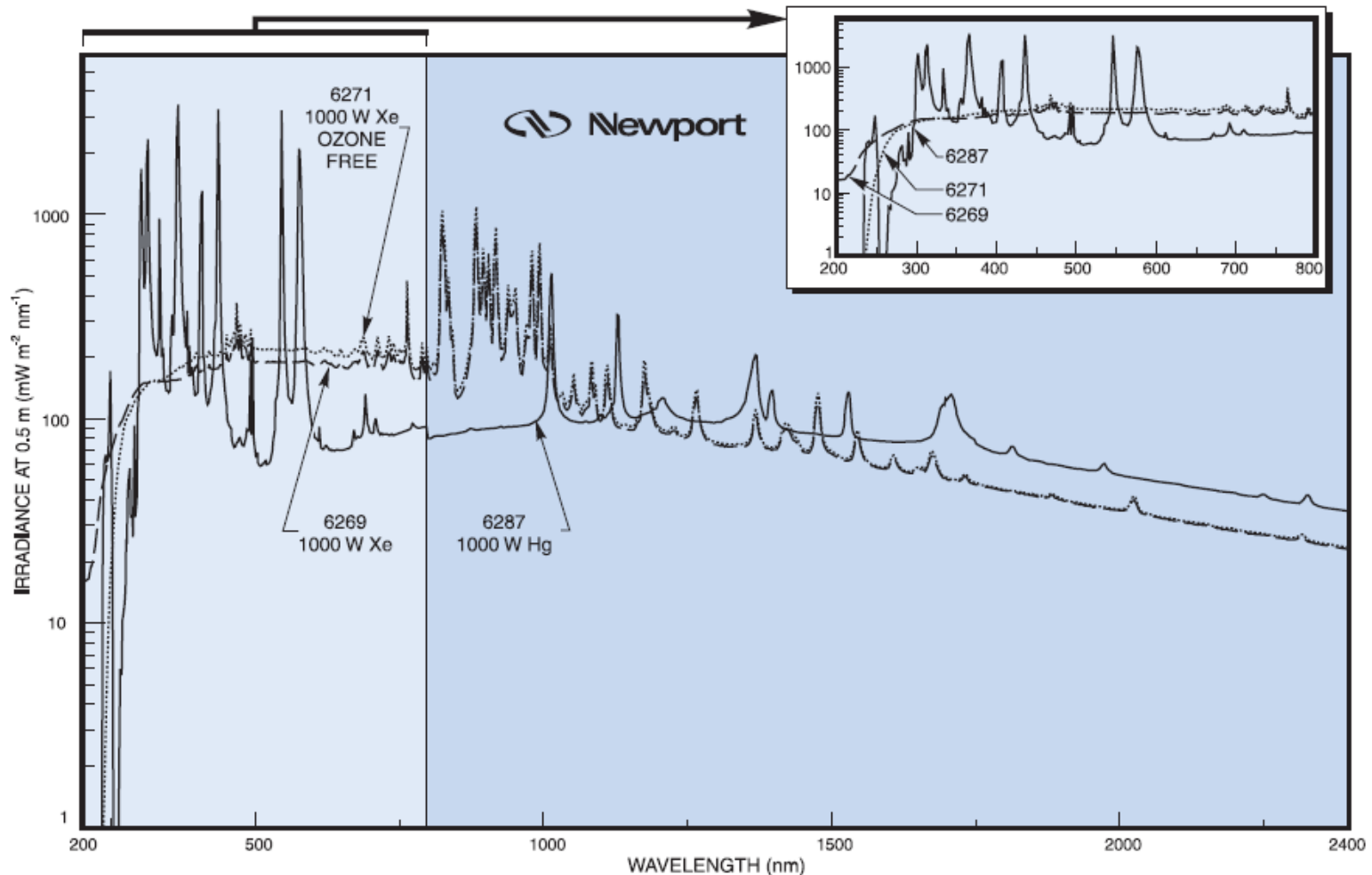
Typical pulsetrain display. The repetition rate shown is 100 Hz, the peak power 4 kW.



Light Sources

Arc Lamps

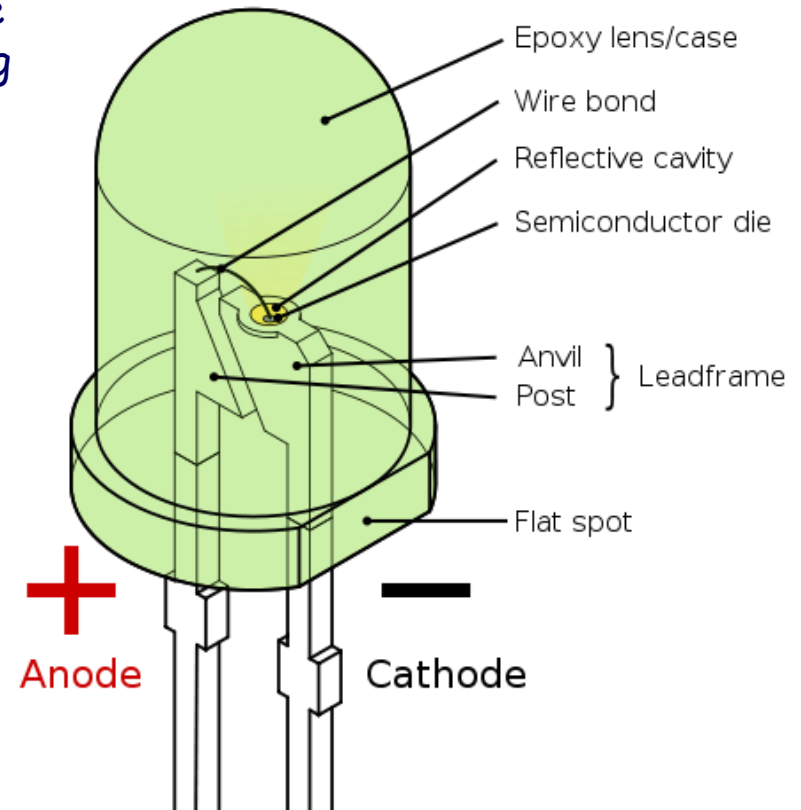
Spectral irradiance of various Arc Lamps



Light Sources

Light emitting diode (LED)

When a light-emitting diode is forward biased (switched on), electrons are able to recombine with electron holes within the device, releasing energy in the form of photons



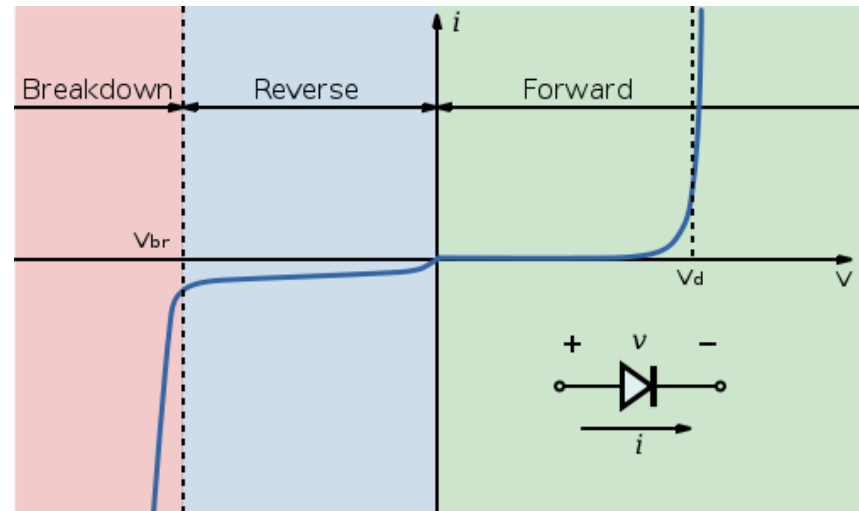
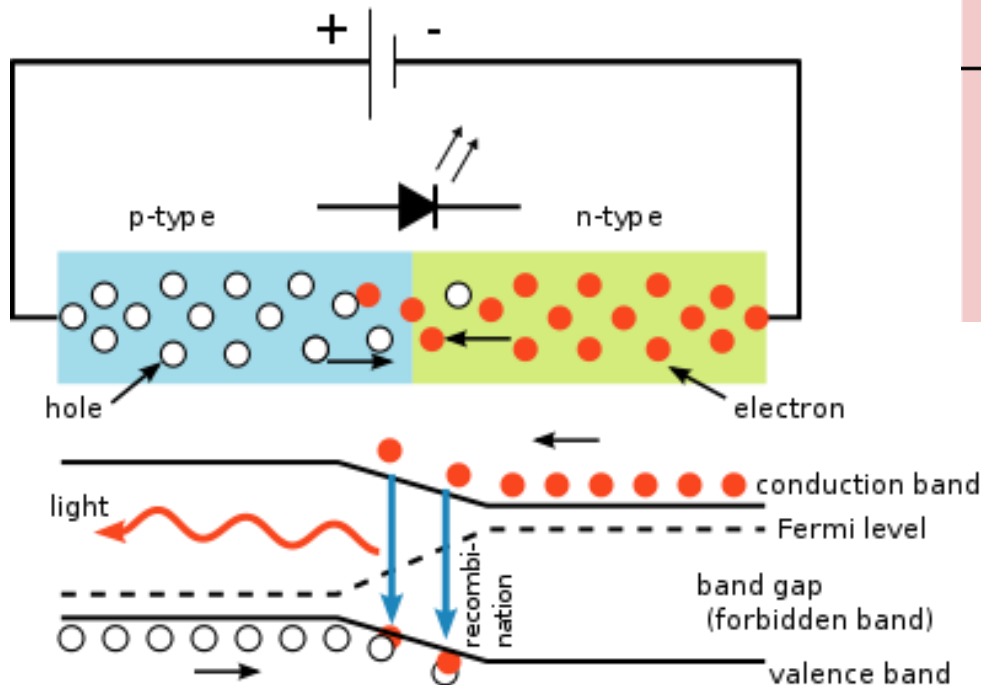
An LED consists of a chip of semiconducting material doped with impurities to create a p-n junction



Light Sources

Light emitting diode (LED)

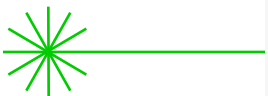
The wavelength of the light emitted, and thus its color depends on the band gap energy of the materials forming the p-n junction



Light Sources

Light emitting diode (LED)

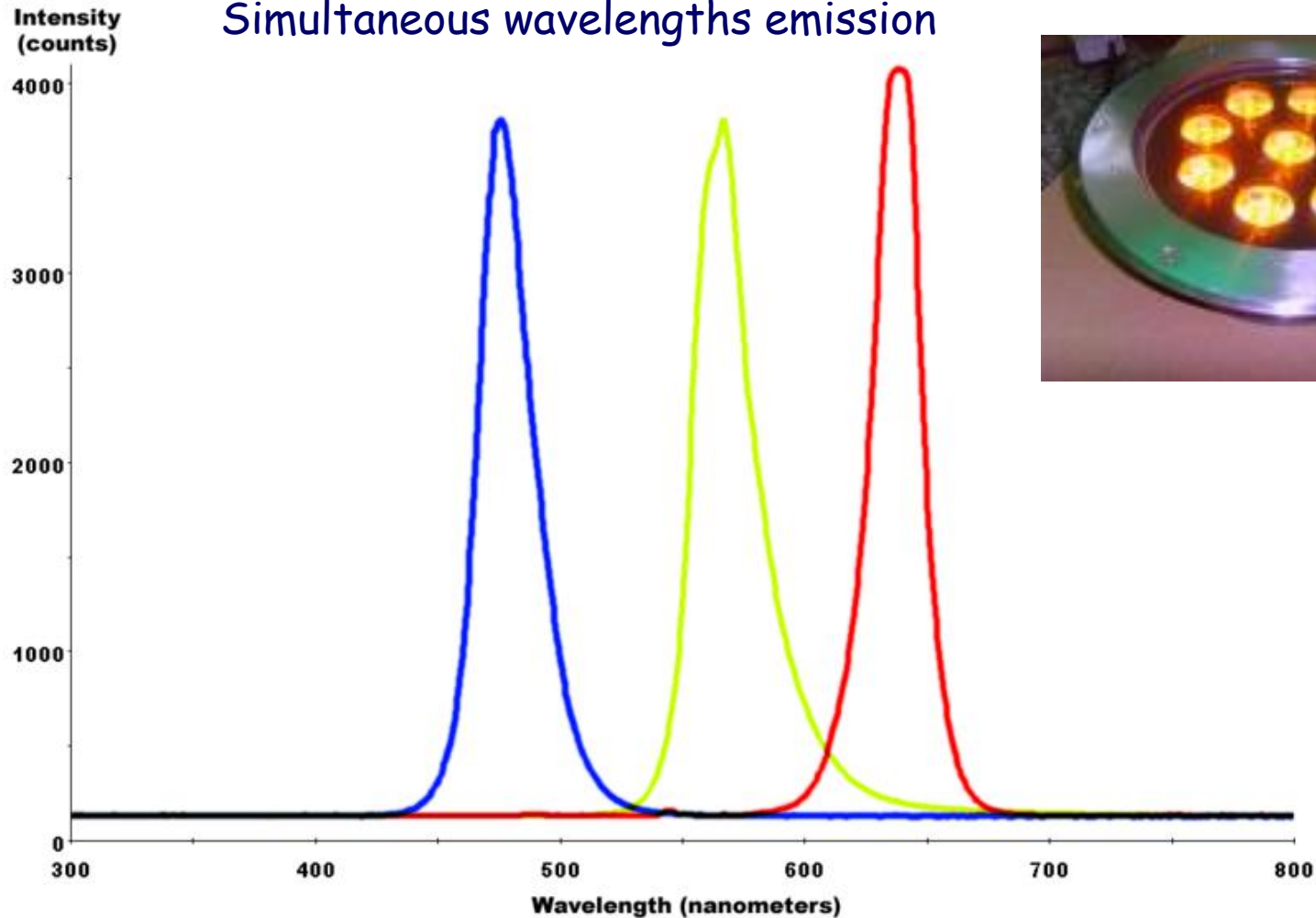
Color	Wavelength [nm]	Voltage [V]	Semiconductor material
Infrared	$\lambda > 760$	$\Delta V < 1.9$	Gallium arsenide (GaAs) Aluminium gallium arsenide (AlGaAs)
Red	$610 < \lambda < 760$	$1.63 < \Delta V < 2.03$	Aluminium gallium arsenide (AlGaAs) Gallium arsenide phosphide (GaAsP) Aluminium gallium indium phosphide (AlGaInP) Gallium(III) phosphide (GaP)
Orange	$590 < \lambda < 610$	$2.03 < \Delta V < 2.10$	Gallium arsenide phosphide (GaAsP) Aluminium gallium indium phosphide (AlGaInP) Gallium(III) phosphide (GaP)
Yellow	$570 < \lambda < 590$	$2.10 < \Delta V < 2.18$	Gallium arsenide phosphide (GaAsP) Aluminium gallium indium phosphide (AlGaInP) Gallium(III) phosphide (GaP)
Green	$500 < \lambda < 570$	$1.9^{[46]} < \Delta V < 4.0$	Indium gallium nitride (InGaN) / Gallium(III) nitride (GaN) Gallium(III) phosphide (GaP) Aluminium gallium indium phosphide (AlGaInP) Aluminium gallium phosphide (AlGaP)
Blue	$450 < \lambda < 500$	$2.48 < \Delta V < 3.7$	Zinc selenide (ZnSe) Indium gallium nitride (InGaN) Silicon carbide (SiC) as substrate Silicon (Si) as substrate – (under development)
Violet	$400 < \lambda < 450$	$2.76 < \Delta V < 4.0$	Indium gallium nitride (InGaN)
Purple	multiple types	$2.48 < \Delta V < 3.7$	Dual blue/red LEDs, blue with red phosphor, or white with purple plastic
Ultraviolet	$\lambda < 400$	$3.1 < \Delta V < 4.4$	Diamond (235 nm) ^[47] Boron nitride (215 nm) ^{[48][49]} Aluminium nitride (AlN) (210 nm) ^[50] Aluminium gallium nitride (AlGaN) Aluminium gallium indium nitride (AlGaInN) – (down to 210 nm)
White	Broad spectrum	$\Delta V = 3.5$	Blue/UV diode with yellow phosphor



Light Sources

Light emitting diode (LED)

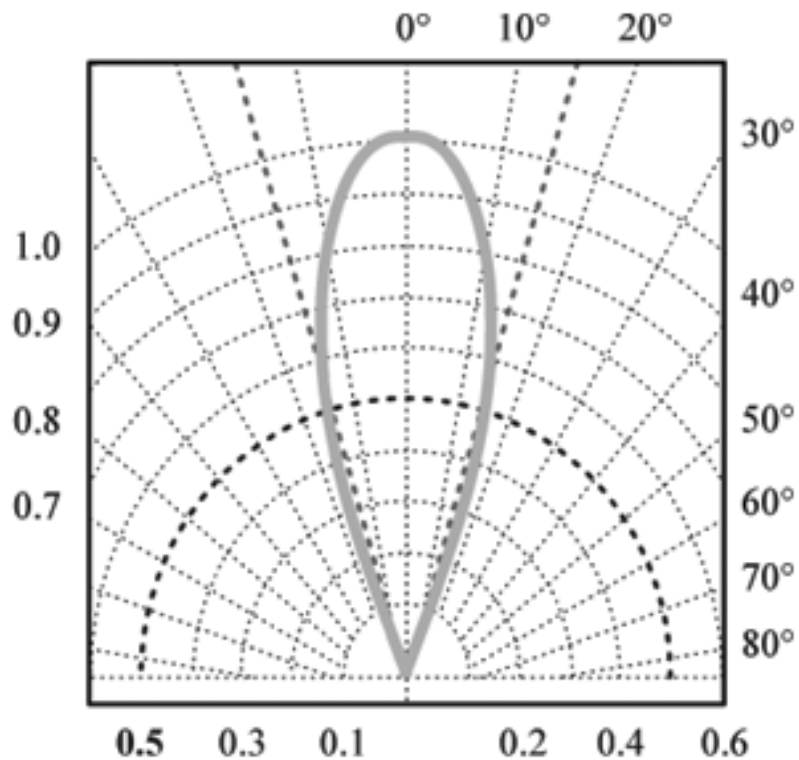
Simultaneous wavelengths emission



Light Sources

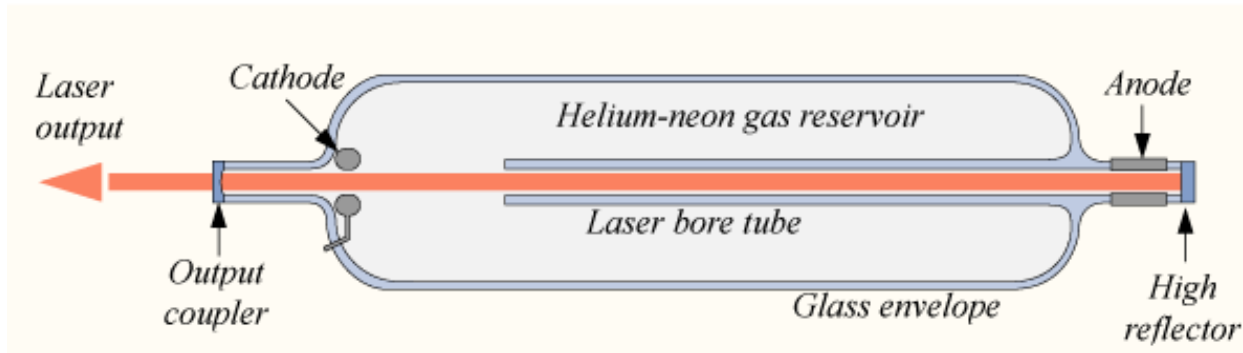
Light emitting diode (LED)

Typical emission flux



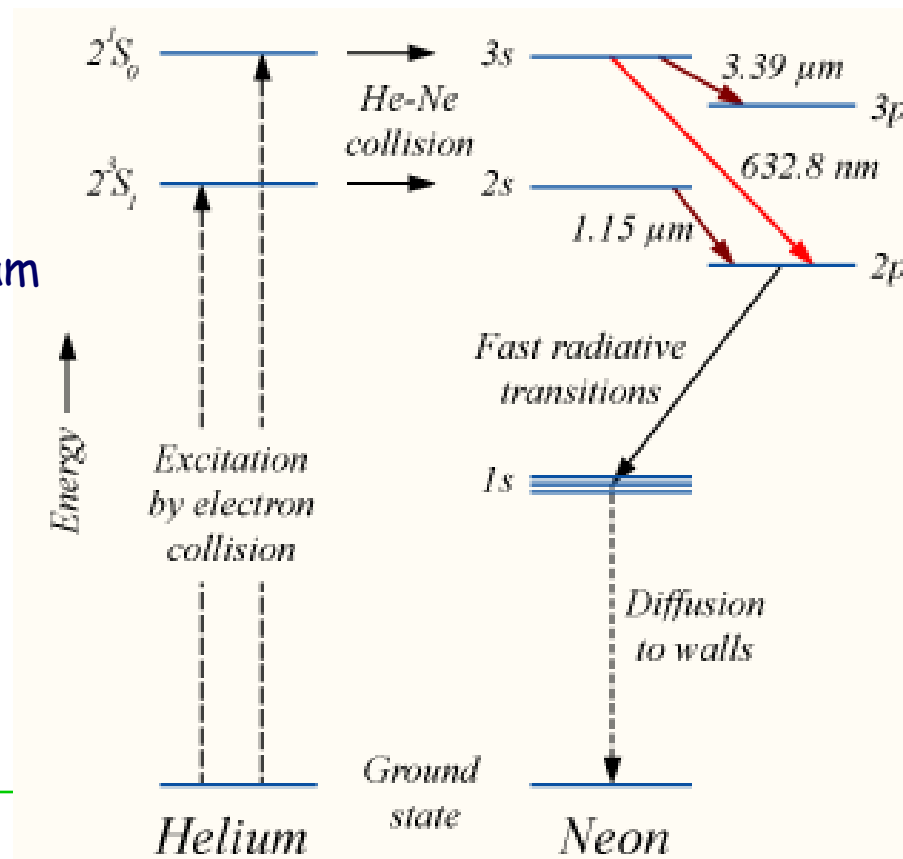
Light Sources

Gas lasers: He-Ne



Schematic diagram of a He-Ne laser

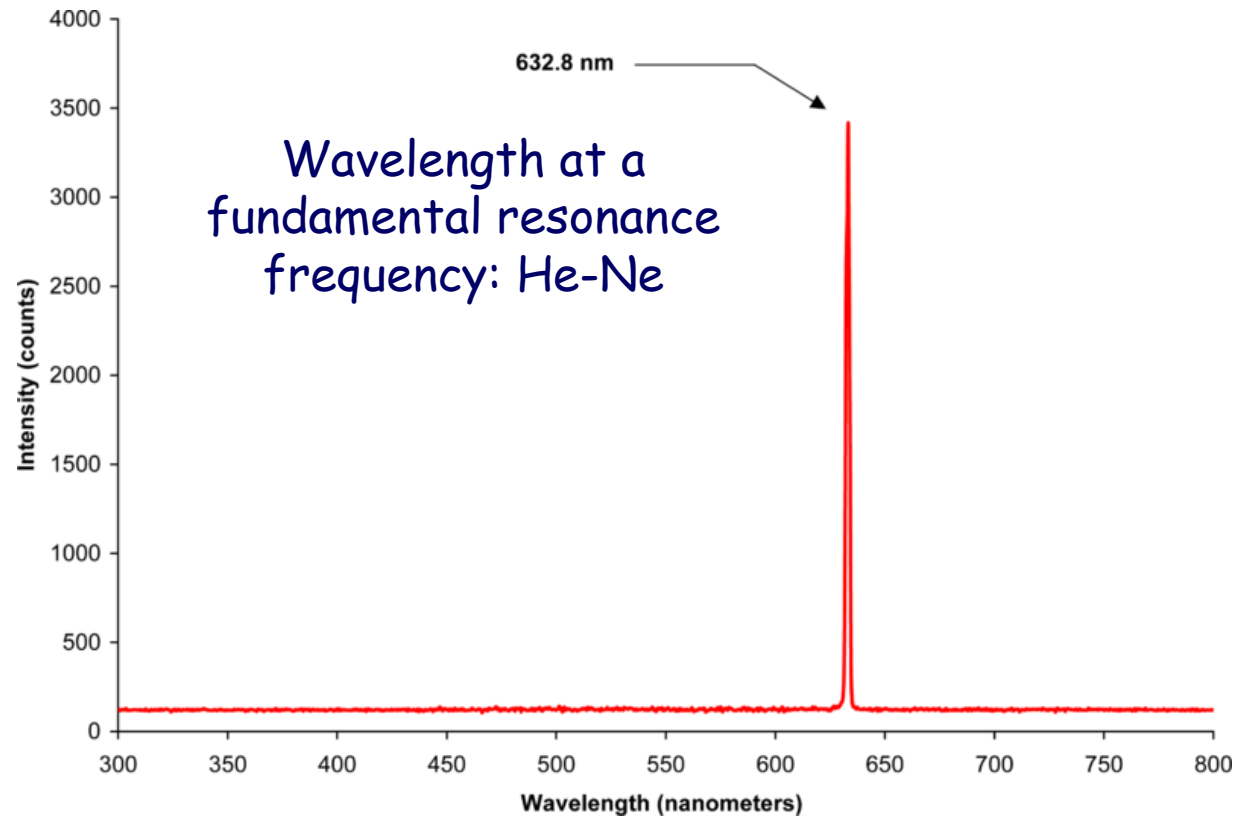
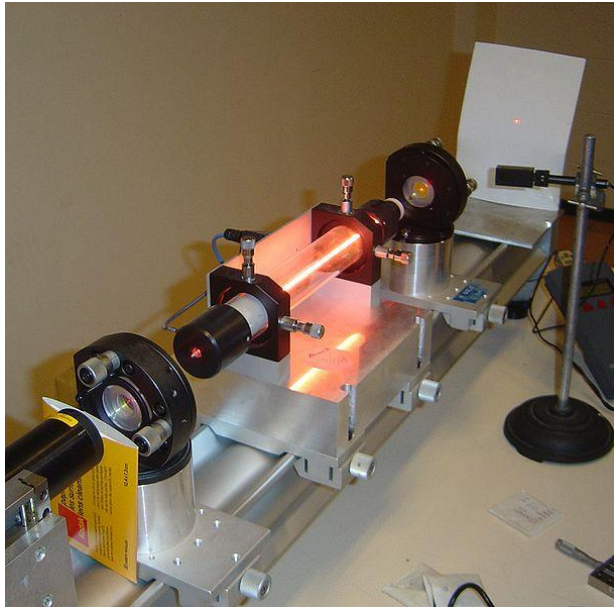
Energy level diagram of a He-Ne laser



Light Sources

Gas lasers: He-Ne

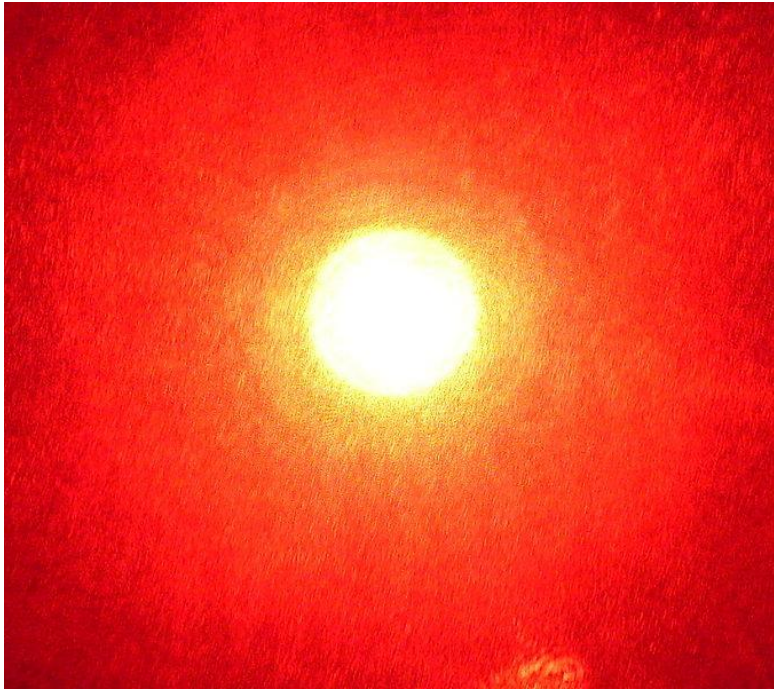
He-Ne laser



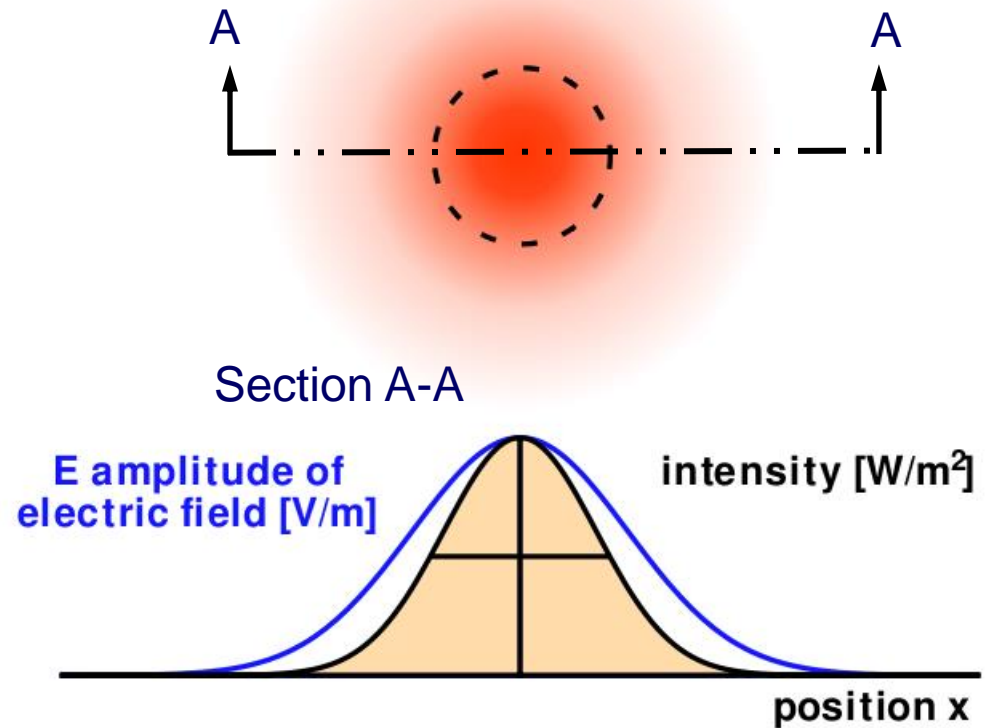
Light Sources

Transversal profile

He-Ne cross section of intensity

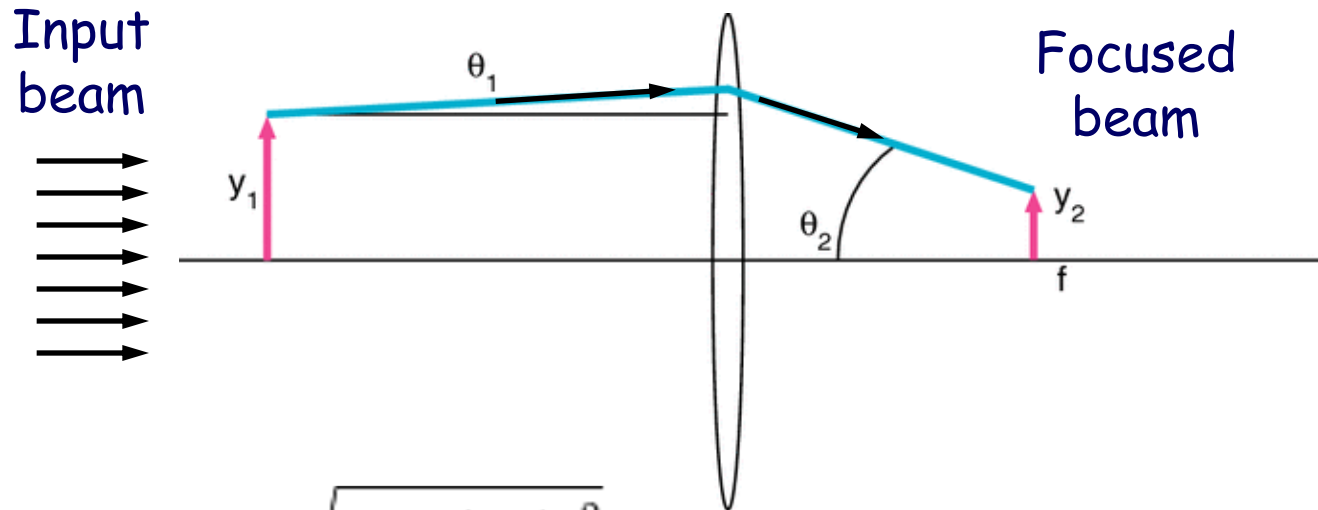


Gaussian intensity distribution



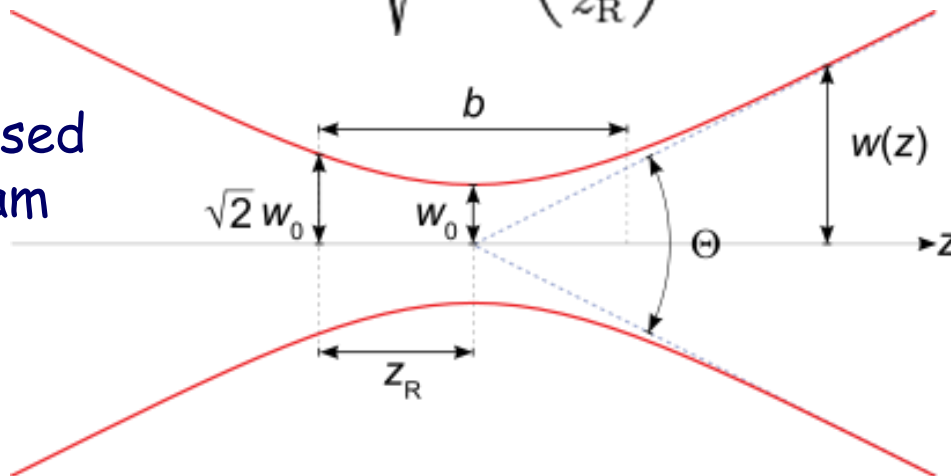
Light Sources

Beam diameter: focused beam



$$w(z) = w_0 \sqrt{1 + \left(\frac{z}{z_R} \right)^2}$$

Focused beam

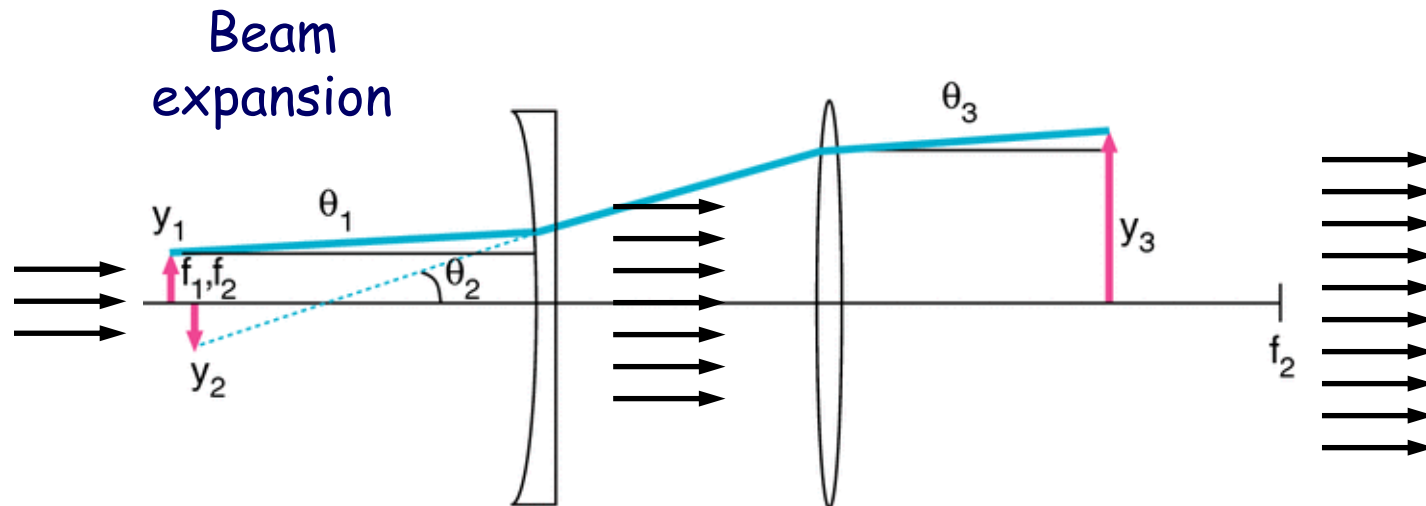
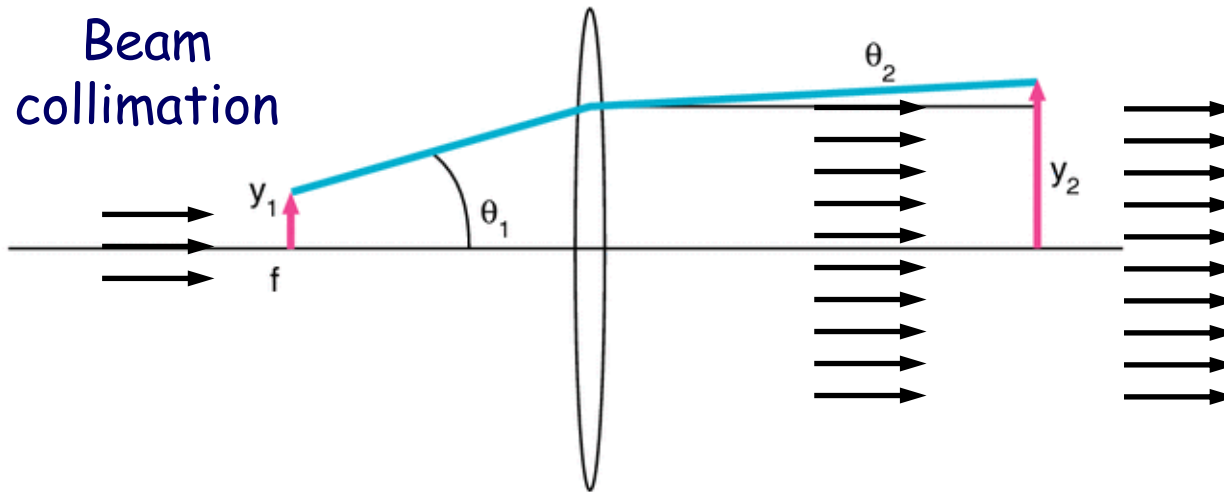


Gaussian beam width
 $w(z)$ as a function of the axial distance z . w_0 : beam waist; b : depth of focus; z_R : Rayleigh range; Θ : total angular spread



Light Sources

Collimation and expansion of a laser beam



Light Sources

Lasers: gas

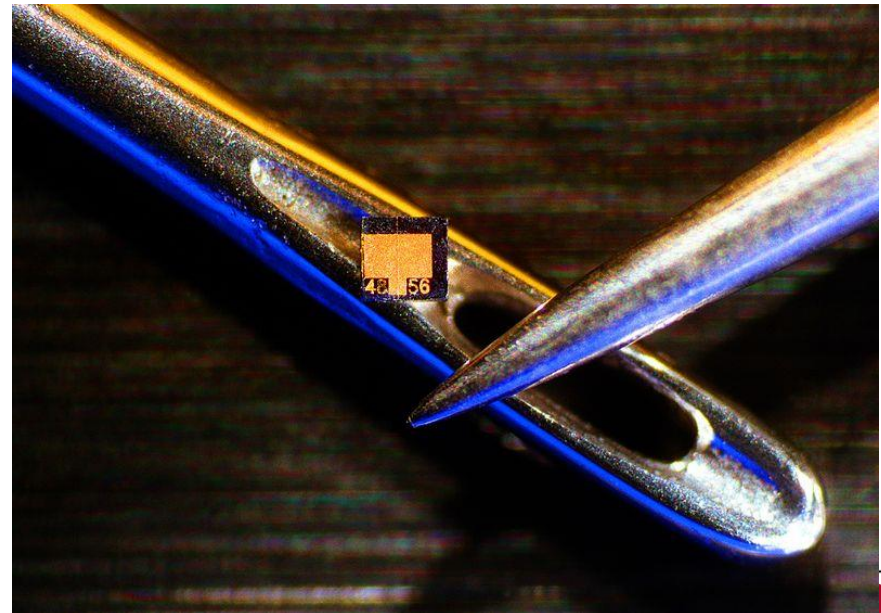
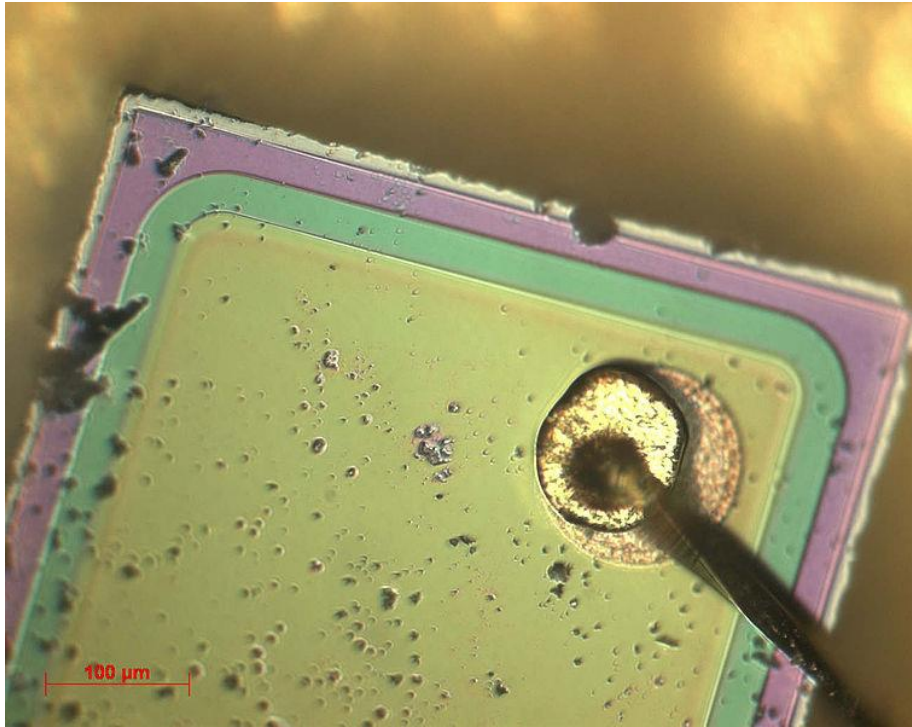
Laser gain medium and type ↕	Operation wavelength(s)	Pump source	Applications and notes
Helium-neon laser	632.8 nm (543.5 nm, 593.9 nm, 611.8 nm, 1.1523 μm, 1.52 μm, 3.3913 μm)	Electrical discharge	Interferometry, holography, spectroscopy, barcode scanning, alignment, optical demonstrations.
Argon laser	454.6 nm, 488.0 nm, 514.5 nm (351 nm, 363.8, 457.9 nm, 465.8 nm, 476.5 nm, 472.7 nm, 528.7 nm, also frequency doubled to provide 244 nm, 257 nm)	Electrical discharge	Retinal phototherapy (for diabetes), lithography, confocal microscopy, spectroscopy pumping other lasers.
Krypton laser	416 nm, 530.9 nm, 568.2 nm, 647.1 nm, 676.4 nm, 752.5 nm, 799.3 nm	Electrical discharge	Scientific research, mixed with argon to create "white-light" lasers, light shows.
Xenon ion laser	Many lines throughout visible spectrum extending into the UV and IR.	Electrical discharge	Scientific research.
Nitrogen laser	337.1 nm	Electrical discharge	Pumping of dye lasers, measuring air pollution, scientific research. Nitrogen lasers can operate superradiantly (without a resonator cavity). Amateur laser construction. See TEA laser
Carbon dioxide laser	10.6 μm, (9.4 μm)	Transverse (high power) or longitudinal (low power) electrical discharge	Material processing (cutting, welding, etc.), surgery.
Carbon monoxide laser	2.6 to 4 μm, 4.8 to 8.3 μm	Electrical discharge	Material processing (engraving, welding, etc.), photoacoustic spectroscopy.
Excimer laser	193 nm (ArF), 248 nm (KrF), 308 nm (XeCl), 353 nm (XeF)	Excimer recombination via electrical discharge	Ultraviolet lithography for semiconductor manufacturing, laser surgery, LASIK.



Light Sources

Laser diodes: semiconductors

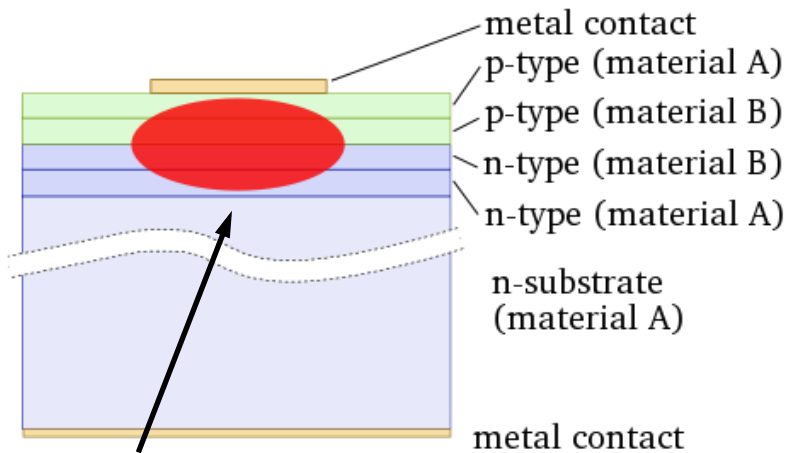
Laser diodes: package
and semiconductor
dies



Light Sources

Laser diodes: semiconductors

Diagram of front view of a double heterostructure laser diode



Elliptical output profile of intensity

Diagram of a simple vertical-cavity surface emitting laser (VCSEL) structure

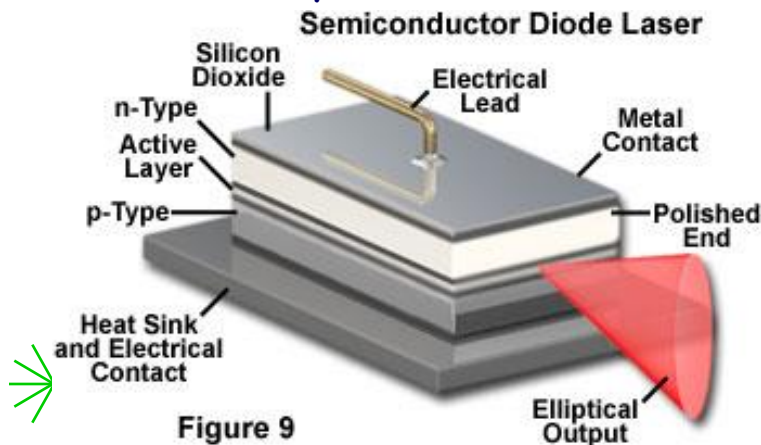
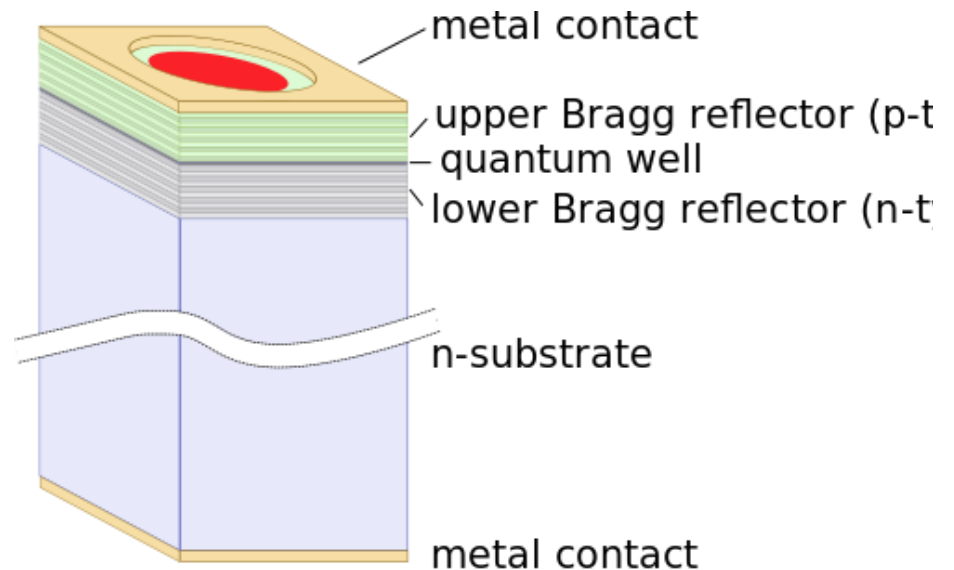
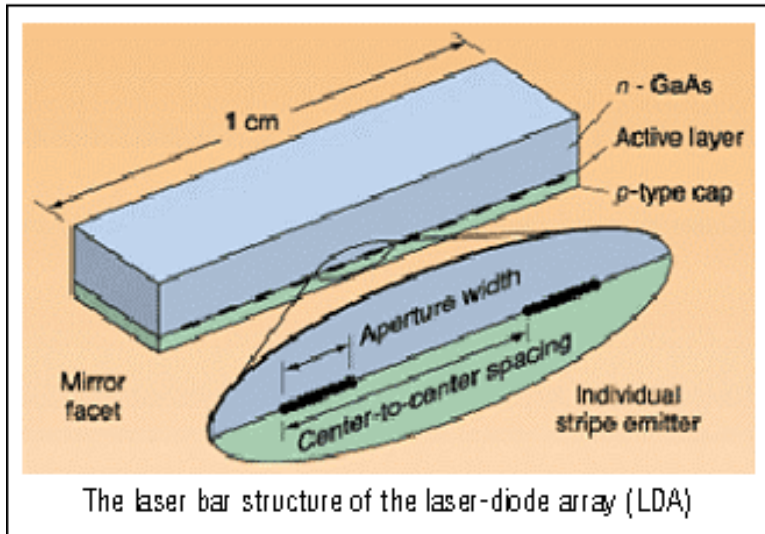


Figure 9

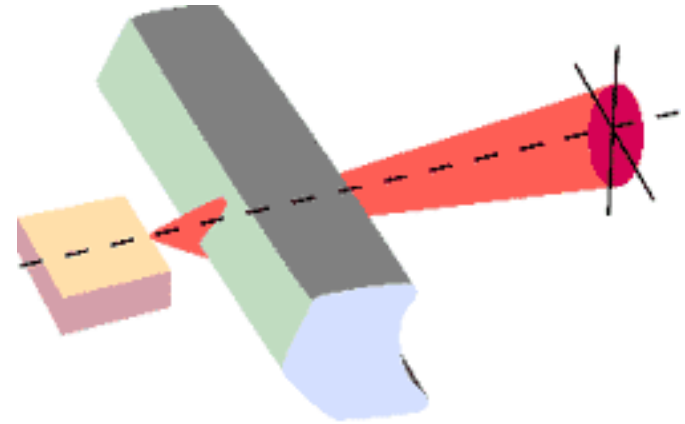
Light Sources

Laser diodes: semiconductors

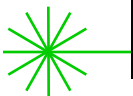
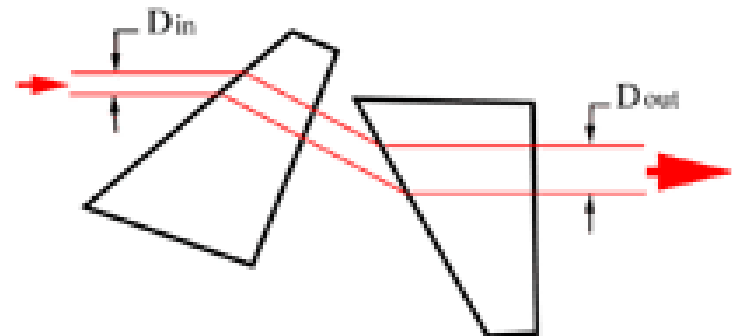
Elliptical output profile of intensity



Cylindrical microlens for laser diode beam correction



Anamorphic prisms for laser diode beam correction



Light Sources

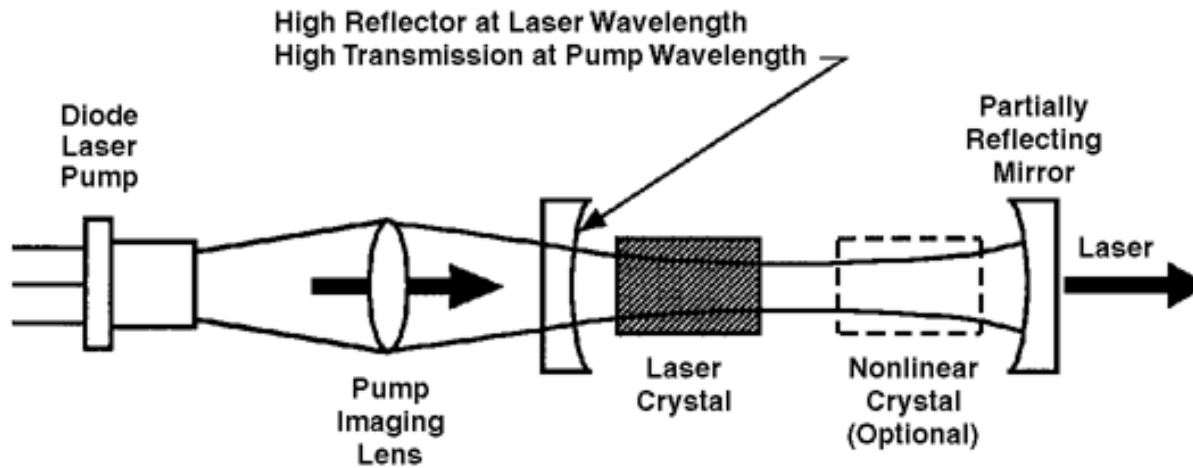
Laser diodes: semiconductors

Laser gain medium and type ↕	Operation wavelength(s)	Pump source	Applications and notes
Semiconductor laser diode (general information)	0.4-20 μm , depending on active region material.	Electrical current	Telecommunications, holography, printing, weapons, machining, welding, pump sources for other lasers.
GaN	0.4 μm		Optical discs. 405 nm is used in Blu-Ray discs reading/recording.
AlGaInP, AlGaAs	0.63-0.9 μm		Optical discs, laser pointers, data communications. 780 nm Compact Disc, 650 nm general DVD player and 635 nm DVD for Authoring recorder laser are the most common lasers type in the world. Solid-state laser pumping, machining, medical.
InGaAsP	1.0-2.1 μm		Telecommunications, solid-state laser pumping, machining, medical..
lead salt	3-20 μm		
Vertical cavity surface emitting laser (VCSEL)	850 - 1500 nm, depending on material		Telecommunications
Quantum cascade laser	Mid-infrared to far-infrared.		Research, Future applications may include collision-avoidance radar, industrial-process control and medical diagnostics such as breath analyzers.
Hybrid silicon laser	Mid-infrared		Research



Light Sources

Solid state lasers



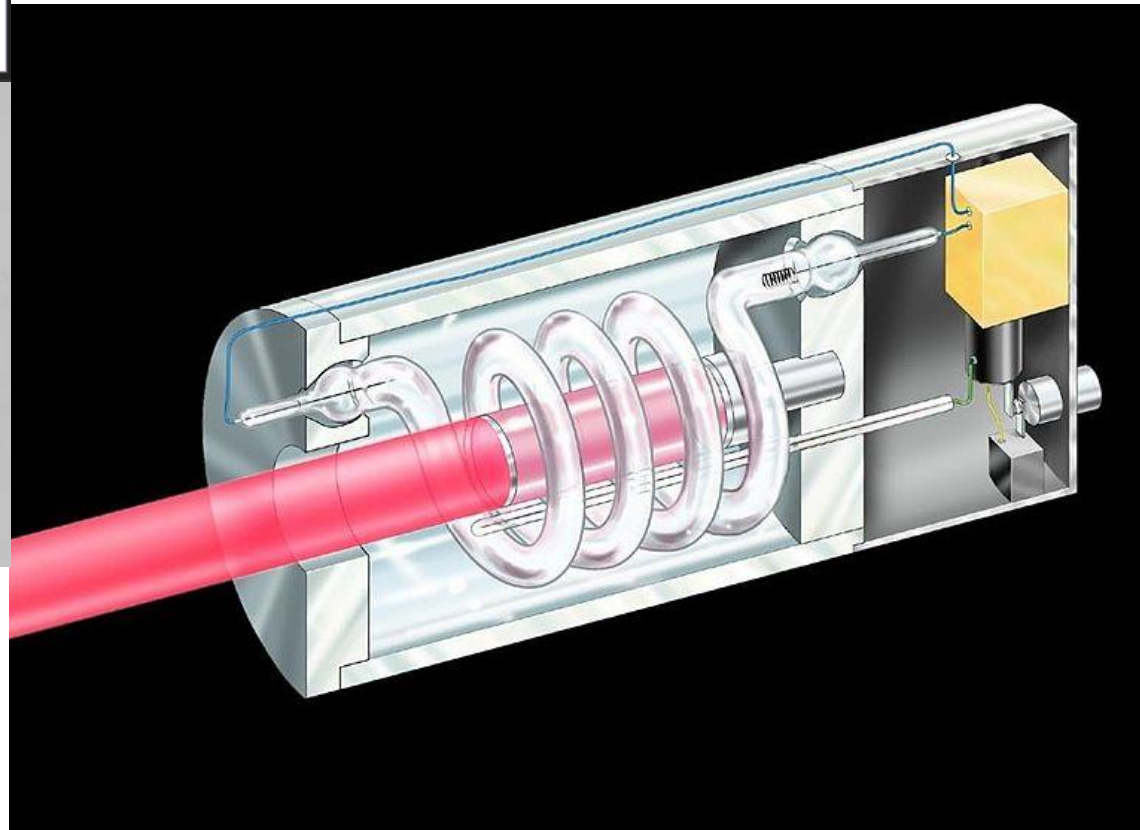
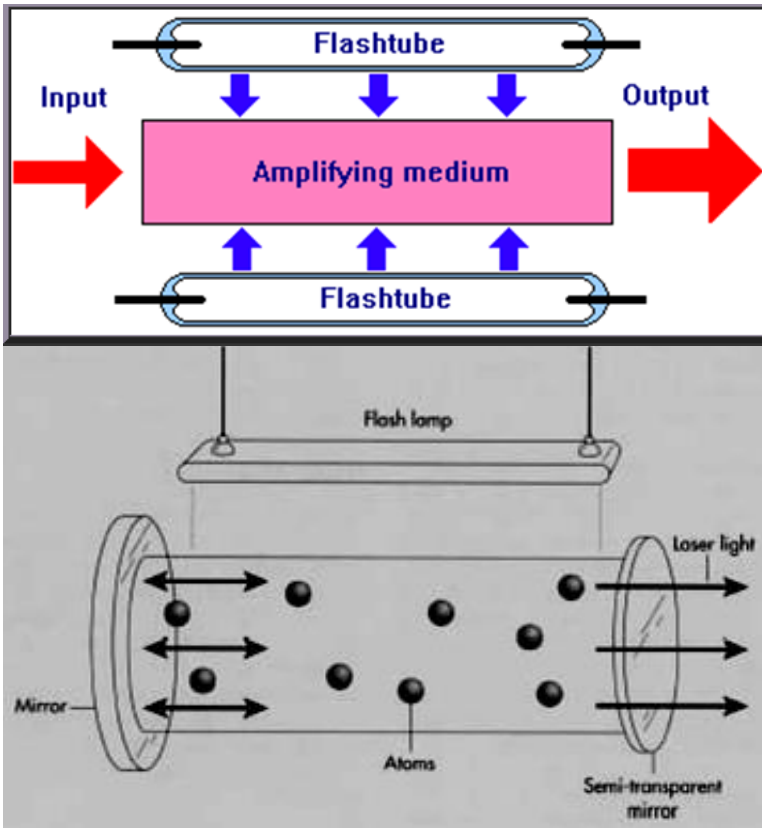
Nd:YAG laser used
as an optical pump



Light Sources

Solid state lasers: Ruby laser - first visible laser invented

Synthetic ruby crystal
used as gain medium



Theodore
Maiman,
1960



Light Sources

Solid state lasers

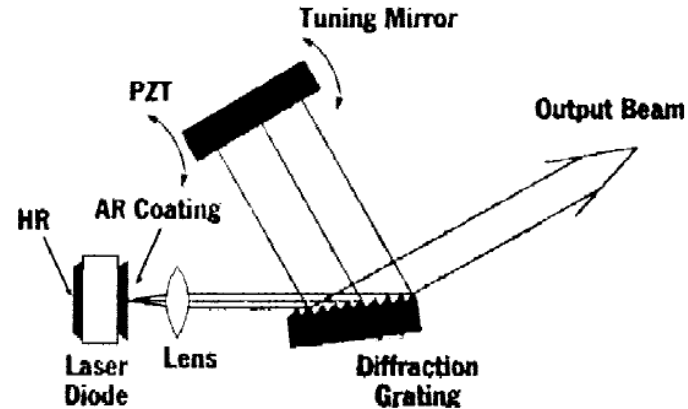
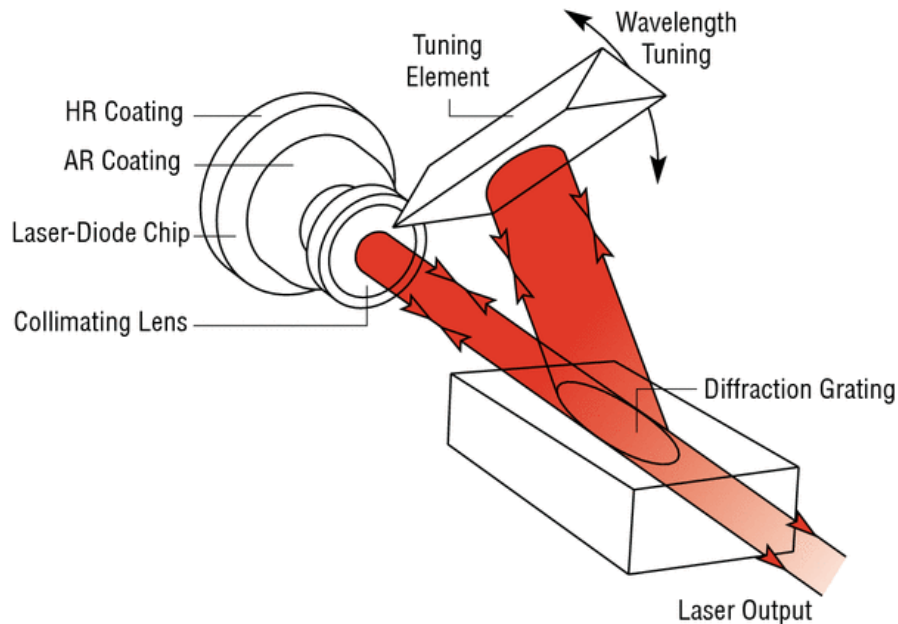
Laser gain medium and type ↕	Operation wavelength(s)	Pump source	Applications and notes
Ruby laser	694.3 nm	Flashlamp	Holography, tattoo removal. The first type of visible light laser invented; May 1960.
Nd:YAG laser	1.064 μm , (1.32 μm)	Flashlamp, laser diode	Material processing, rangefinding, laser target designation, surgery, research, pumping other lasers (combined with frequency doubling to produce a green 532 nm beam). One of the most common high power lasers. Usually pulsed (down to fractions of a nanosecond)
Er:YAG laser	2.94 μm	Flashlamp, laser diode	Periodontal scaling, Dentistry
Neodymium YLF (Nd:YLF) solid-state laser	1.047 and 1.053 μm	Flashlamp, laser diode	Mostly used for pulsed pumping of certain types of pulsed Ti:sapphire lasers, combined with frequency doubling.
Neodymium doped Yttrium orthovanadate (Nd:YVO ₄) laser	1.064 μm	laser diode	Mostly used for continuous pumping of mode-locked Ti:sapphire or dye lasers, in combination with frequency doubling. Also used pulsed for marking and micromachining. A frequency doubled nd:YVO ₄ laser is also the normal way of making a green laser pointer.
Neodymium doped yttrium calcium oxoborate Nd:YCa ₄ O(BO ₃) ₃ or simply Nd:YCOB	~1.060 μm (~530 nm at second harmonic)	laser diode	Nd:YCOB is a so called "self-frequency doubling" or SFD laser material which is both capable of lasing and which has nonlinear characteristics suitable for second harmonic generation. Such materials have the potential to simplify the design of high brightness green lasers.
Neodymium glass (Nd:Glass) laser	~1.062 μm (Silicate glasses), ~1.054 μm (Phosphate	Flashlamp, laser diode	Used in extremely high power (terawatt scale), high energy (megajoules) multiple beam systems for inertial confinement fusion. Nd:Glass lasers are usually frequency tripled to the



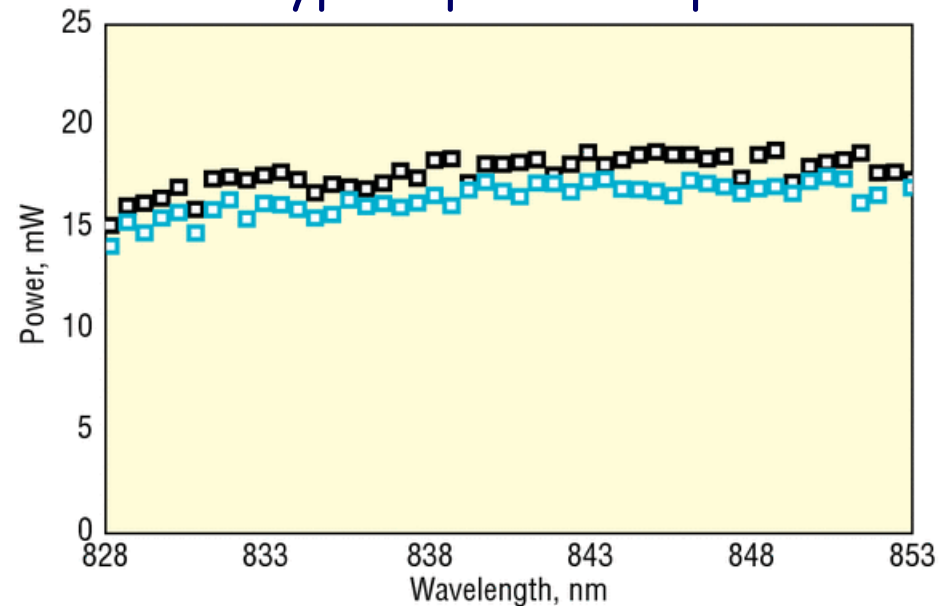
Light Sources

Semiconductor, tunable lasers

Modified Littman-Metcalf configuration (external cavity)



Typical power output



Announcements

- Next class: project for this class; list of topics (CF) and teams (Students)
- Laboratory visit(s) - after class today/next class

Assignment, due next lecture:

- a) Reading: Chapter 2 of Yoshizawa:
Lenses/Prisms/Mirrors
- b) Homework: Problems Ch02 - see website of our course

